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PRODUCT RELIABILITY REPORT
FOR

DS1267B

Maxim Integrated Products

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Prepared by:

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Conclusion:

The following qualification successfully meets the quality and reliability standards required of all Maxim products:

DS1267B

In addition, Maxim's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

Device Description:

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

AfT = exp((Ea/k)*(1/Tu - 1/Ts)) = tu/ts
AfT = Acceleration factor due to Temperature
tu = Time at use temperature (e.g. 55°C)
ts = Time at stress temperature (e.g. 125°C)
k = Boltzmann's Constant (8.617 x 10-5 eV/°K)
Tu = Temperature at Use (°K)
Ts = Temperature at Stress (°K)
Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

AfV = exp(B*(Vs - Vu))
AfV = Acceleration factor due to Voltage
Vs = Stress Voltage (e.g. 7.0 volts)
Vu = Maximum Operating Voltage (e.g. 5.5 volts)
B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

Fr = X/(ts * AfV * AfT * N * 2)
X = Chi-Sq statistical upper limit
N = Life test sample size

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE:	**MTTF (YRS):**	**1805**	**FITS:**	**63.2**
	DEVICE HOURS:	**14487047**	**FAILS:**	**0**

Only data from Operating Life or similar stresses are used for this calculation.

The parameters used to calculate this failure rate are as follows:

Cf: 60% **Ea: 0.7** **B: 0** **Tu: 25 °C** **Vu: 5.5 Volts**

The reliability data follows. At the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data. **Bold** Product Number denotes specific product data.

Device Information:

Process:	MFN, B3, 8inch Silicon Gate 3um with Epi and Isolation.
Passivation:	400nm Oxide 400nm Nitride
Die Size:	113 x 179
Number of Transistors:	3680
Interconnect:	Aluminum / 0.5% Copper
Gate Oxide Thickness:	NA

ESD HBM

DESCRIPTION	DATE CODE/PRODUCT/LOT#			CONDITION	READPOINT		QTY	FAILS	FA#
ESD SENSITIVITY	1210	**DS1868B**	QM220405A	JESD22-A114 HBM 500 VOLTS	1	PUL'S	5	0	
ESD SENSITIVITY	1210	**DS1868B**	QM220405A	JESD22-A114 HBM 1000 VOLTS	1	PUL'S	5	0	
ESD SENSITIVITY	1210	**DS1868B**	QM220405A	JESD22-A114 HBM 1500 VOLTS	1	PUL'S	5	0	
ESD SENSITIVITY	1210	**DS1868B**	QM220405A	JESD22-A114 HBM 2000 VOLTS	1	PUL'S	5	0	
ESD SENSITIVITY	1210	**DS1868B**	QM220405A	JESD22-A114 HBM 2500 VOLTS	1	PUL'S	5	5	No FA
					Total:			**5**	

LATCH-UP

DESCRIPTION	DATE CODE/PRODUCT/LOT#			CONDITION	READPOINT	QTY	FAILS	FA#
LATCH-UP I	1210	**DS1868B**	QM220405A	JESD78A, I-TEST 25C 85mA		6	0	
LATCH-UP V	1210	**DS1868B**	QM220405A	JESD78A, V-SUPPLY TEST 25C		6	0	
					Total:		**0**	

OPERATING LIFE

DESCRIPTION	DATE CODE/PRODUCT/LOT#	CONDITION	READPOINT	QTY	FAILS	FA#

HIGH TEMP OP LIFE	1210	**DS1868B**	QM220405A	125C, 5.5 VOLTS	192	HRS	80	0
					Total:			**0**

FAILURE RATE:	**MTTF (YRS):**	**1805**	**FITS:**	**63.2**
	DEVICE HOURS:	**14487047**	**FAILS:**	**0**

Note 1: Latchup I-test passed +/-100mA except for the Sout pin which passes -85mA and fails -100mA. Note 2: Cumulative monitor data for the B3 Process results in a FIT Rate of 0.03 @ 25C and 0.53 @ 55C (0.8 eV, 60% UCL).